



# PSMN4R3-80PS

N-channel 80 V, 4.3 mΩ standard level MOSFET in TO220

Rev. 03 — 18 April 2011

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175°C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

### 1.3 Applications

- DC-to-DC converters
- Motor control
- Load switch
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	80	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see <a href="#">Figure 1</a>	<a href="#">[1]</a>	-	120	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	-	306	W
$T_j$	junction temperature		-55	-	175	°C

#### Static characteristics

$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $T_j = 25\text{ °C};$ see <a href="#">Figure 13</a>	<a href="#">[2]</a>	-	3.7	4.3	mΩ
		$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $T_j = 100\text{ °C};$ see <a href="#">Figure 12</a>	<a href="#">[2]</a>	-	6.1	7.1	mΩ



**Table 1. Quick reference data ...continued**

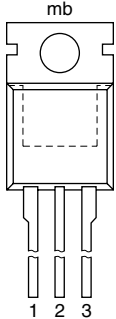
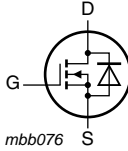
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 75\text{ A};$	-	28.4	-	nC
$Q_{G(\text{tot})}$	total gate charge	$V_{DS} = 40\text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	111	-	nC
<b>Avalanche ruggedness</b>						
$E_{DS(\text{AL})S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ °C};$ $I_D = 120\text{ A}; V_{\text{sup}} \leq 80\text{ V};$ $R_{GS} = 50\text{ }\Omega;$ unclamped	-	-	676	mJ

[1] Continuous current is limited by package

[2] Measured 3 mm from package.

## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	drain		

**SOT78 (TO-220AB)**

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		Version
	Name	Description	
PSMN4R3-80PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

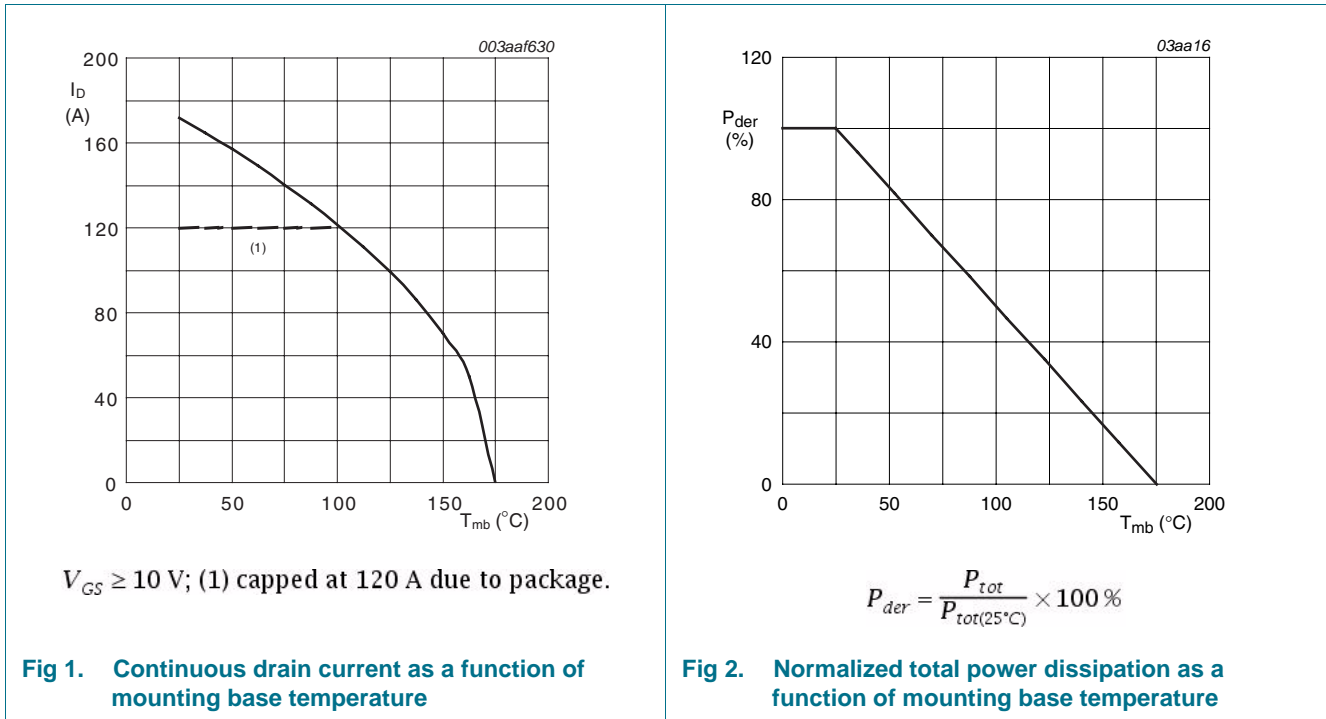
### 4. Limiting values

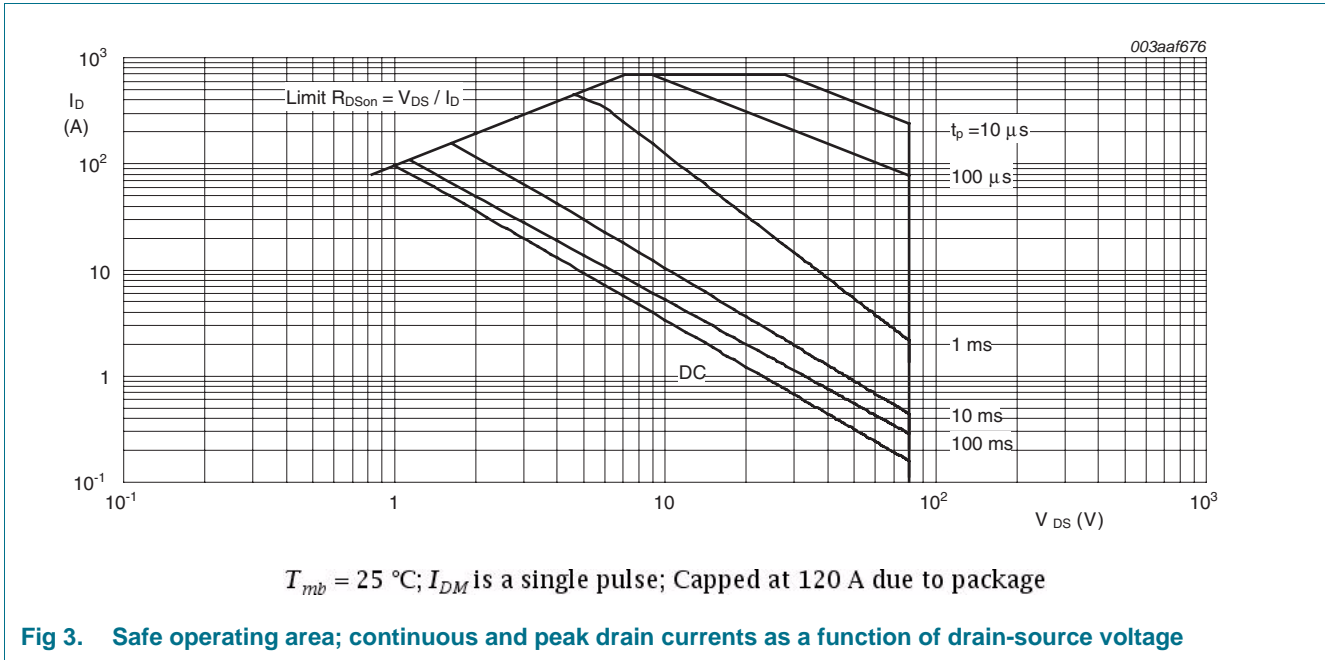
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	80	V	
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	80	V	
V <sub>GS</sub>	gate-source voltage		-20	20	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <a href="#">Figure 1</a> [1]	-	120	A	
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 1</a> [1]	-	120	A	
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 3</a>	-	688	A	
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <a href="#">Figure 2</a>	-	306	W	
T <sub>stg</sub>	storage temperature		-55	175	°C	
T <sub>j</sub>	junction temperature		-55	175	°C	
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C	
<b>Source-drain diode</b>						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C	-	688	A	
<b>Avalanche ruggedness</b>						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	V <sub>GS</sub> = 10 V; T <sub>j(initial)</sub> = 25 °C; I <sub>D</sub> = 120 A; V <sub>sup</sub> ≤ 80 V; R <sub>GS</sub> = 50 Ω; unclamped	-	676	mJ	

[1] Continuous current is limited by package

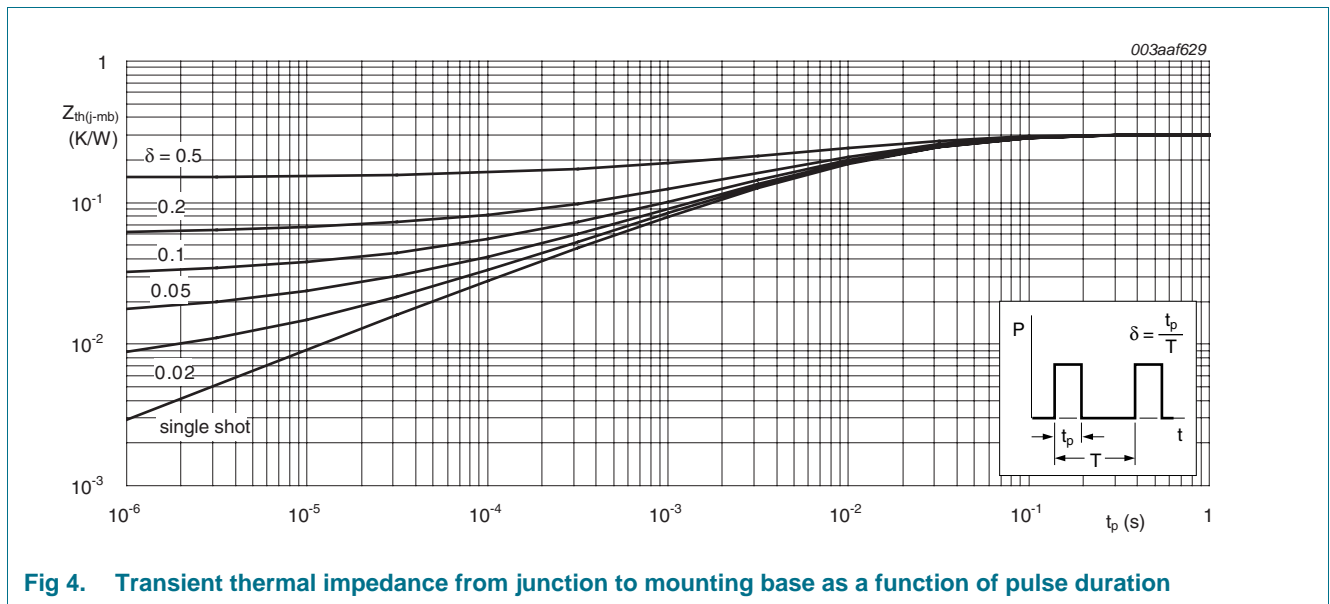




### 5. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	0.3	0.49	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W



**Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration**

## 6. Characteristics

**Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
<b>Static characteristics</b>							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	73	-	-	V	
		$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	80	-	-	V	
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	1	-	-	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	-	-	4.6	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a> ; see <a href="#">Figure 11</a>	2	3	4	V	
$I_{DSS}$	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.02	10	$\mu\text{A}$	
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	$\mu\text{A}$	
$I_{GSS}$	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	-	100	nA	
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	-	100	nA	
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a>	[1]	-	8.9	10.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a>	[1]	-	3.7	4.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a>	[1]	-	6.1	7.1	mΩ
$R_G$	internal gate resistance (AC)	$f = 1 \text{ MHz}$	-	0.9	-	Ω	
<b>Dynamic characteristics</b>							
$Q_{G(tot)}$	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	104	-	nC	
		$I_D = 75 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	111	-	nC	
$Q_{GS}$	gate-source charge		-	38	-	nC	
$Q_{GS(th)}$	pre-threshold gate-source charge		-	24.1	-	nC	
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	14.1	-	nC	
$Q_{GD}$	gate-drain charge		-	28.4	-	nC	
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	6.1	-	V	
$C_{iss}$	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 16</a>	-	8161	-	pF	
$C_{oss}$	output capacitance		-	701	-	pF	
$C_{rss}$	reverse transfer capacitance		-	337	-	pF	
$t_{d(on)}$	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 0.53 \text{ } \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 4.7 \text{ } \Omega; I_D = 75 \text{ A}$	-	38	-	ns	
$t_r$	rise time		-	29	-	ns	
$t_{d(off)}$	turn-off delay time		-	94	-	ns	
$t_f$	fall time		-	33	-	ns	

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 17</a>	-	-	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}$ ; $di_S/dt = 100\text{ A}/\mu\text{s}$ ;	-	59	-	ns
$Q_r$	recovered charge	$V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$	-	109	-	nC

[1] Measured 3 mm from package.

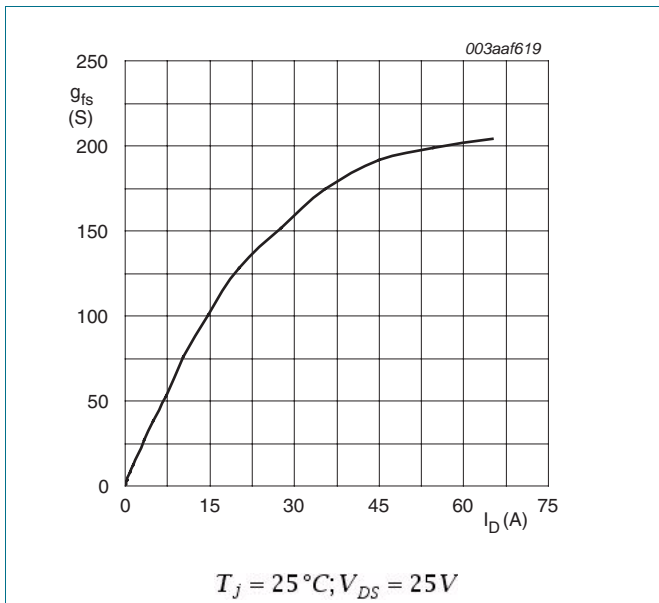


Fig 5. Forward transconductance as a function of drain current; typical values

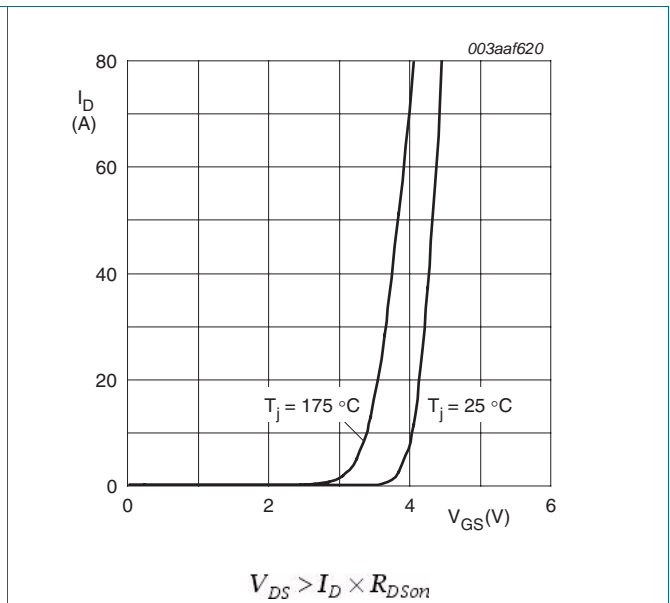


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

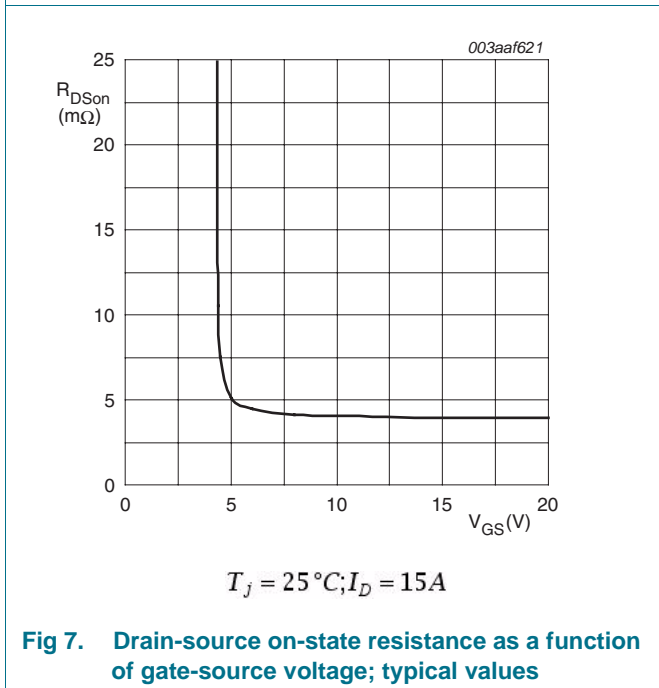


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

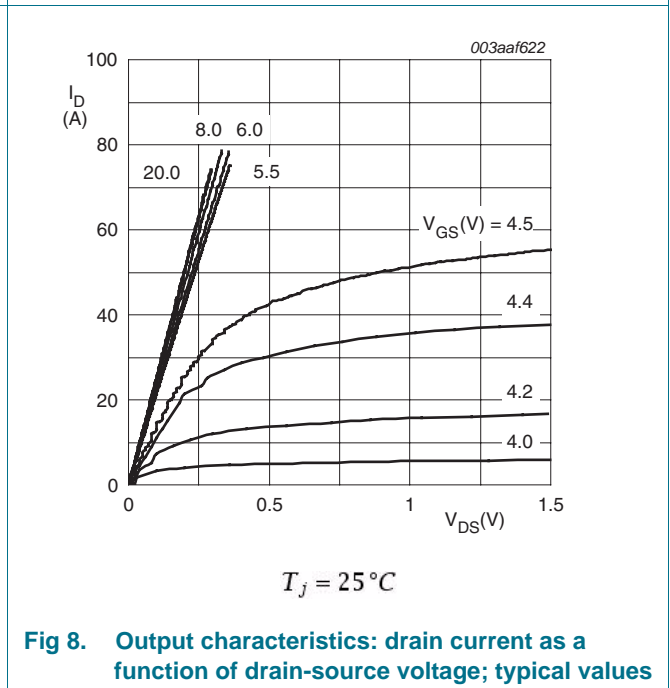
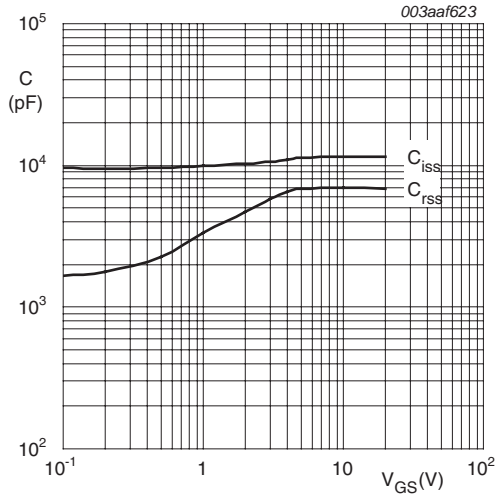
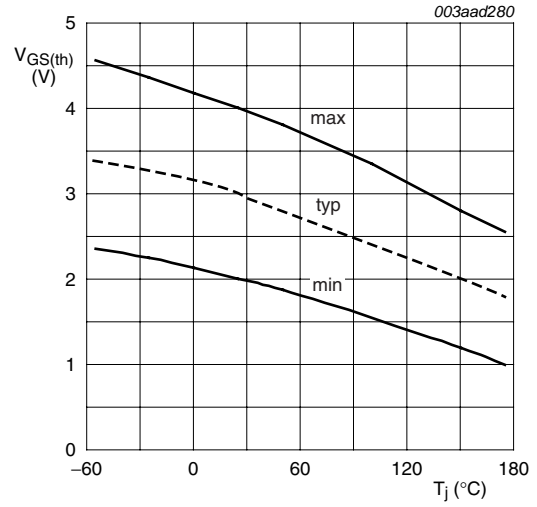


Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values



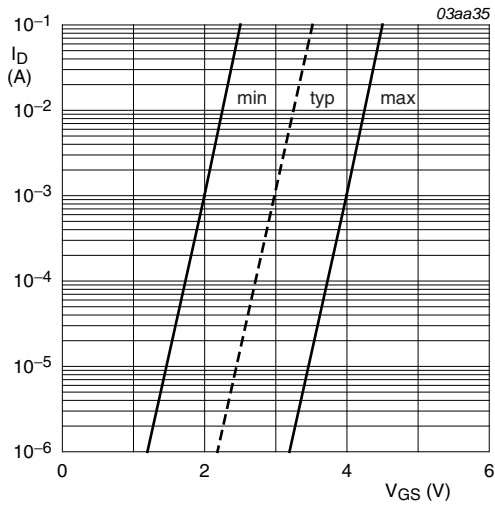
$$V_{DS} = 0V; f = 1MHz$$

Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



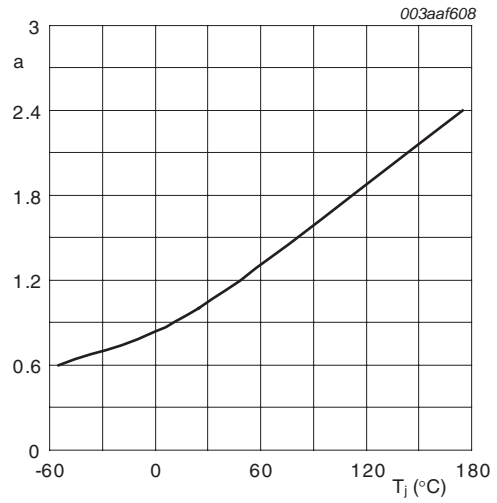
$$I_D = 1\text{ mA}; V_{DS} = V_{GS}$$

Fig 10. Gate-source threshold voltage as a function of junction temperature



$$T_j = 25^\circ C; V_{DS} = 5V$$

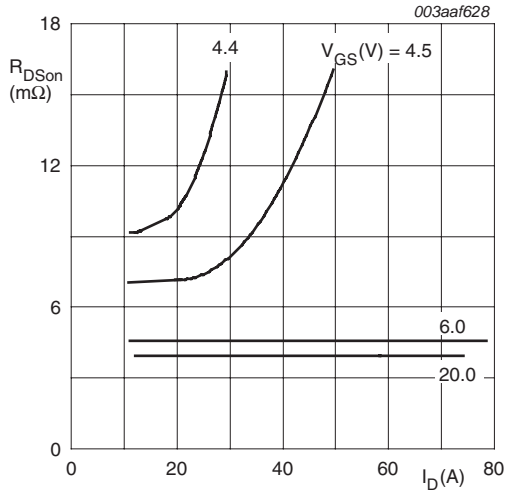
Fig 11. Sub-threshold drain current as a function of gate-source voltage



$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature





$T_j = 25^\circ\text{C}; I_D = 25\text{A}$

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

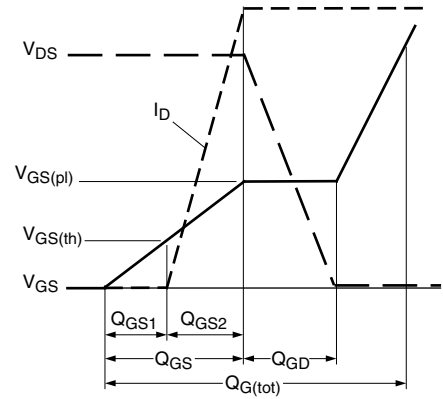
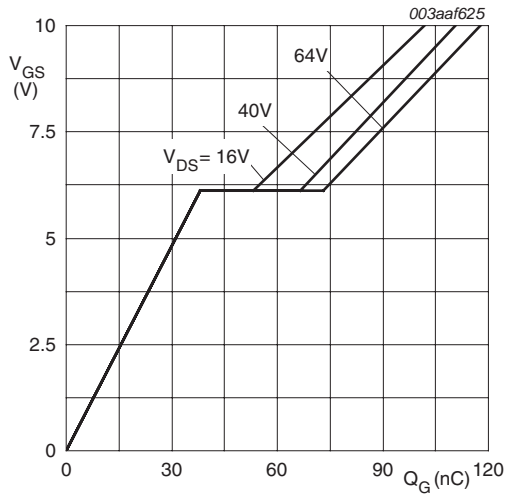
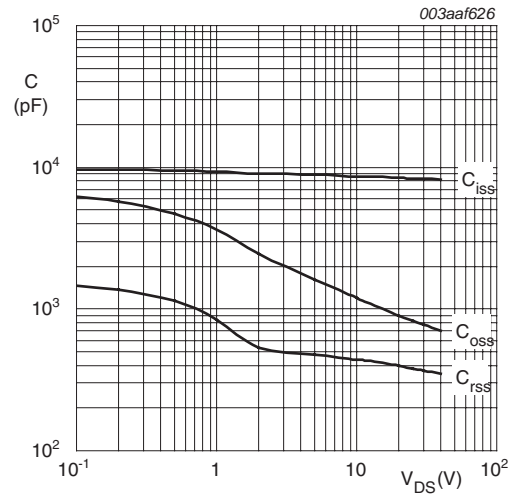


Fig 14. Gate charge waveform definitions



$I_D = 75\text{A}$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{V}; f = 1\text{MHz}$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

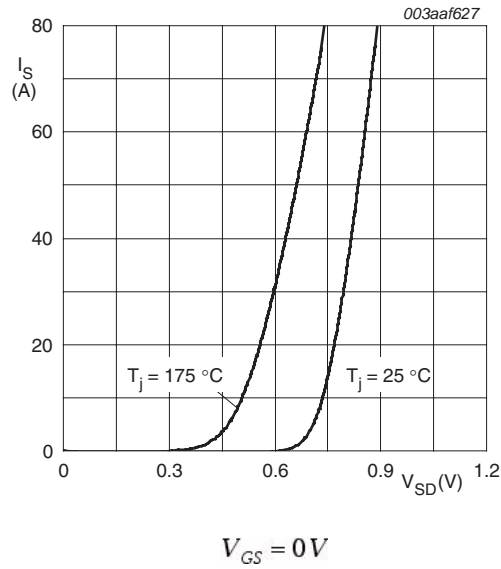


Fig 17. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

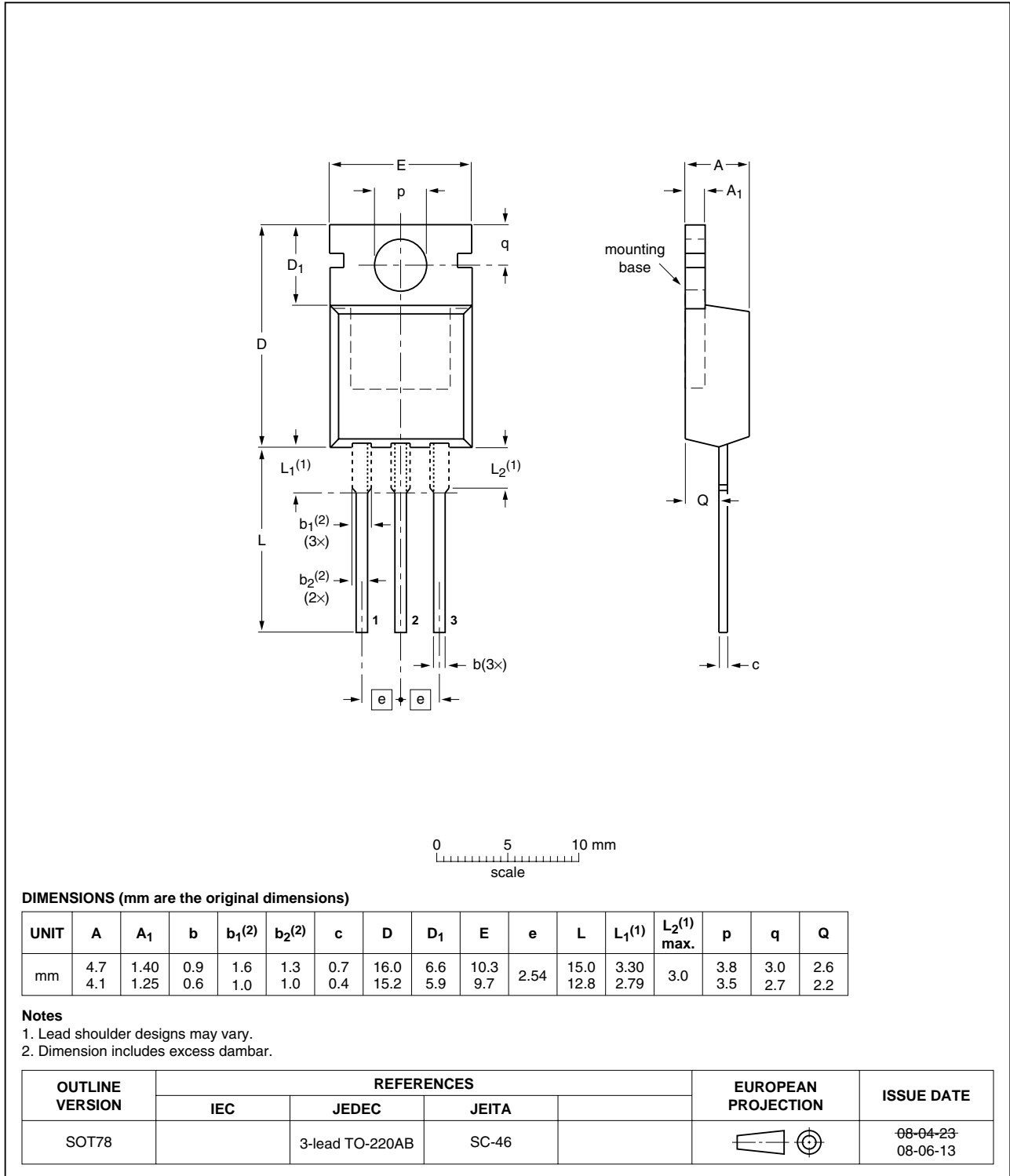


Fig 18. Package outline SOT78 (TO-220AB)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R3-80PS v.3	20110418	Product data sheet	-	PSMN4R3-80PS v.2
Modifications:	<ul style="list-style-type: none"><li>• Status changed from objective to product.</li><li>• Various changes to content.</li></ul>			
PSMN4R3-80PS v.2	20110309	Objective data sheet	-	PSMN4R3-80PS v.1

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1]</sup> <sup>[2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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